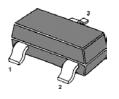


NPN Silicon Epitaxial Planar Transistor

Features

- Halogen and Antimony Free(HAF), RoHS compliant
- AEC-Q101 Qualified
- For switching and amplifier





1.Base 2. Emitter 3. Collector



Mechanical Data

- SOT-23 Plastic Package
- Mounting position: Any

Absolute Maximum Ratings (T _A =25°C unless otherwise noted)				
Parameter	Symbol	Value	Unit	
Collector Base Voltage	V _{CBO}	60	V	
Collector Emitter Voltage	V _{CEO}	40	V	
Emitter Base Voltage	V _{EBO}	6	V	
Collector Current	Ic	200	mA	
Power Dissipation	PD	350	mW	
Operating Junction Temperature Range	TJ	- 55 to + 150	°C	
Storage Temperature Range	Tstg	- 55 to + 150	°C	

Thermal Characteristics					
Parameter	Symbol	Value	Unit		
Thermal Resistance Junction to Ambient ¹⁾	R _{thJA}	357	°C/W		

¹⁾ Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.



Electrical Characteristics (T _A =25°C unless otherwise noted)					
Parameter	Symbol	Min.	Тур.	Max.	Unit
DC Current Gain at $V_{CE} = 1 \text{ V}$, $I_C = 0.1 \text{ mA}$ at $V_{CE} = 1 \text{ V}$, $I_C = 1 \text{ mA}$ at $V_{CE} = 1 \text{ V}$, $I_C = 10 \text{ mA}$ at $V_{CE} = 1 \text{ V}$, $I_C = 50 \text{ mA}$ at $V_{CE} = 1 \text{ V}$, $I_C = 100 \text{ mA}$	h _{FE}	40 70 100 60 30	- - - -	- - 300 - -	- - - -
Collector Base Cutoff Current at $V_{CB} = 30 \text{ V}$	Ісво	-	-	50	nA
Emitter Base Cutoff Current at V _{EB} = 6 V	I _{EBO}	-	-	50	nA
Collector Base Breakdown Voltage at I _C = 10 µA	V _{(BR)CBO}	60	-	-	V
Collector Emitter Breakdown Voltage at I _C = 1 mA	V _(BR) CEO	40	-	-	٧
Emitter Base Breakdown Voltage at I _E = 10 μA	V _{(BR)EBO}	6	-	-	V
Collector Emitter Saturation Voltage at $I_C = 10$ mA, $I_B = 1$ mA at $I_C = 50$ mA, $I_B = 5$ mA	V _{CE(sat)}			0.2 0.3	V
Base Emitter Saturation Voltage at $I_C = 10$ mA, $I_B = 1$ mA at $I_C = 50$ mA, $I_B = 5$ mA	V _{BE(sat)}	0.65		0.85 0.95	V
Current Gain Bandwidth Product at V _{CE} = 20 V, I _C = 10 mA, f = 100 MHz	f⊤	300	-	-	MHz
Collector Output Capacitance at V _{CB} = 5 V, f = 1 MHz	C _{ob}	-	-	4	pF
Delay Time at $V_{CC} = 3 \text{ V}$, $V_{BE} = 0.5 \text{ V}$, $I_C = 10 \text{ mA}$, $I_{B1} = 1 \text{ mA}$	td	-	-	35	ns
Rise Time at $V_{CC} = 3 \text{ V}$, $V_{BE} = 0.5 \text{ V}$, $I_C = 10 \text{ mA}$, $I_{B1} = 1 \text{ mA}$	tr	-	-	35	ns
Storage Time at $V_{CC} = 3 \text{ V}$, $I_C = 10 \text{ mA}$, $I_{B1} = -I_{B2} = 1 \text{ mA}$	ts	-	-	200	ns
Fall Time at $V_{CC} = 3 \text{ V}$, $I_C = 10 \text{ mA}$, $I_{B1} = -I_{B2} = 1 \text{ mA}$	t _f	-	-	50	ns





Typical Characteristics Curves (TA = 25°C unless otherwise noted)

Fig. 1 Output Characteristics Curve

Fig. 2 Collector Current vs. Base to Emitter Voltage

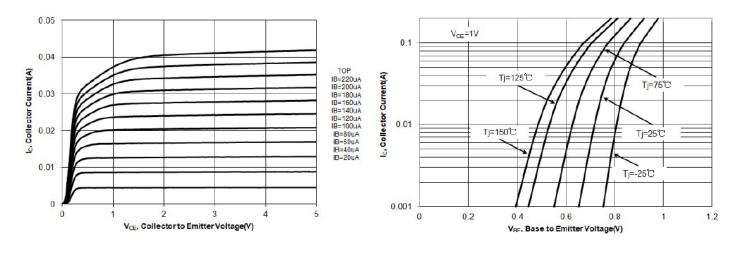


Fig. 3 DC Current Gain vs. Collector Current

Fig. 4 V_{BE(sat)} vs. Collector Current

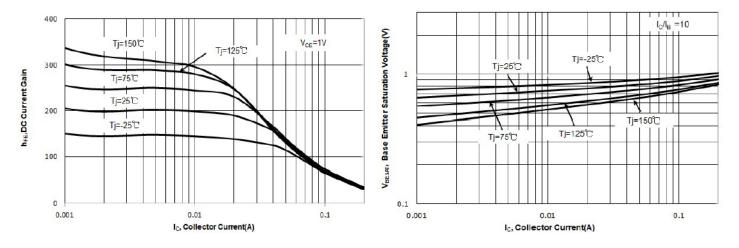
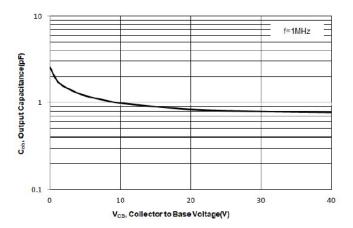
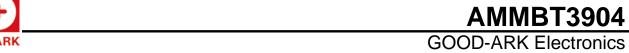


Fig. 5 V_{CE(sat)} vs. Collector Current

VCESAR, Collector Emitter Saturation Voltage(V) Tj=125℃ Tj=25℃ Tj=75℃ 0.001 Ic, Collector Current(A)

Fig. 6 Output Capacitance



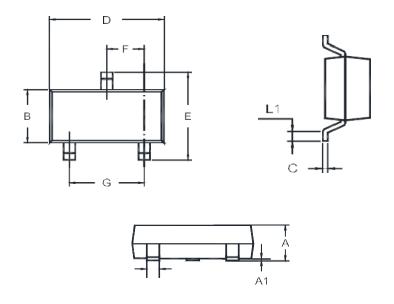


P_{tots} Total Power Disspation(mW) T_a, Ambient Temperature(°C)

Fig. 7 Power Derating Curve

Package Outline Dimensions (Unit: millimeters)



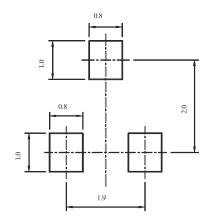


SYMBOL	MILLIMETER			
STIVIBOL	MIN	TYP	MAX	
А	0.89	/	1.2	
A1	0.013	/	0.1	
В	1.2	/	1.4	
С	0.08	/	0.19	
D	2.8	/	3.04	
Е	2.2	/	2.6	
F	0.89	/	1.02	
G	1.78	/	2.04	
L	0.37	/	0.51	
L1	/	/	0.2	



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Recommended Soldering Footprint (Unit: millimeters)



Packing Information

Package	Tape Width	Pitch		Reel Size		Per Reel Packing	
SOT 22	mm	mm	inch	mm	inch	Quantity	
SOT-23	8	4±0.1	0.157±0.004	178	7	3000	

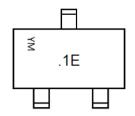
Marking information

" 1E " = Part No. (See table of Marking information)

" YM " = Date Code Marking

" • " = Automotive-grade material

Font type: Arial



Revision History

Version	Date	Major Changes
Rev.A	2025.01.19	Official Release



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